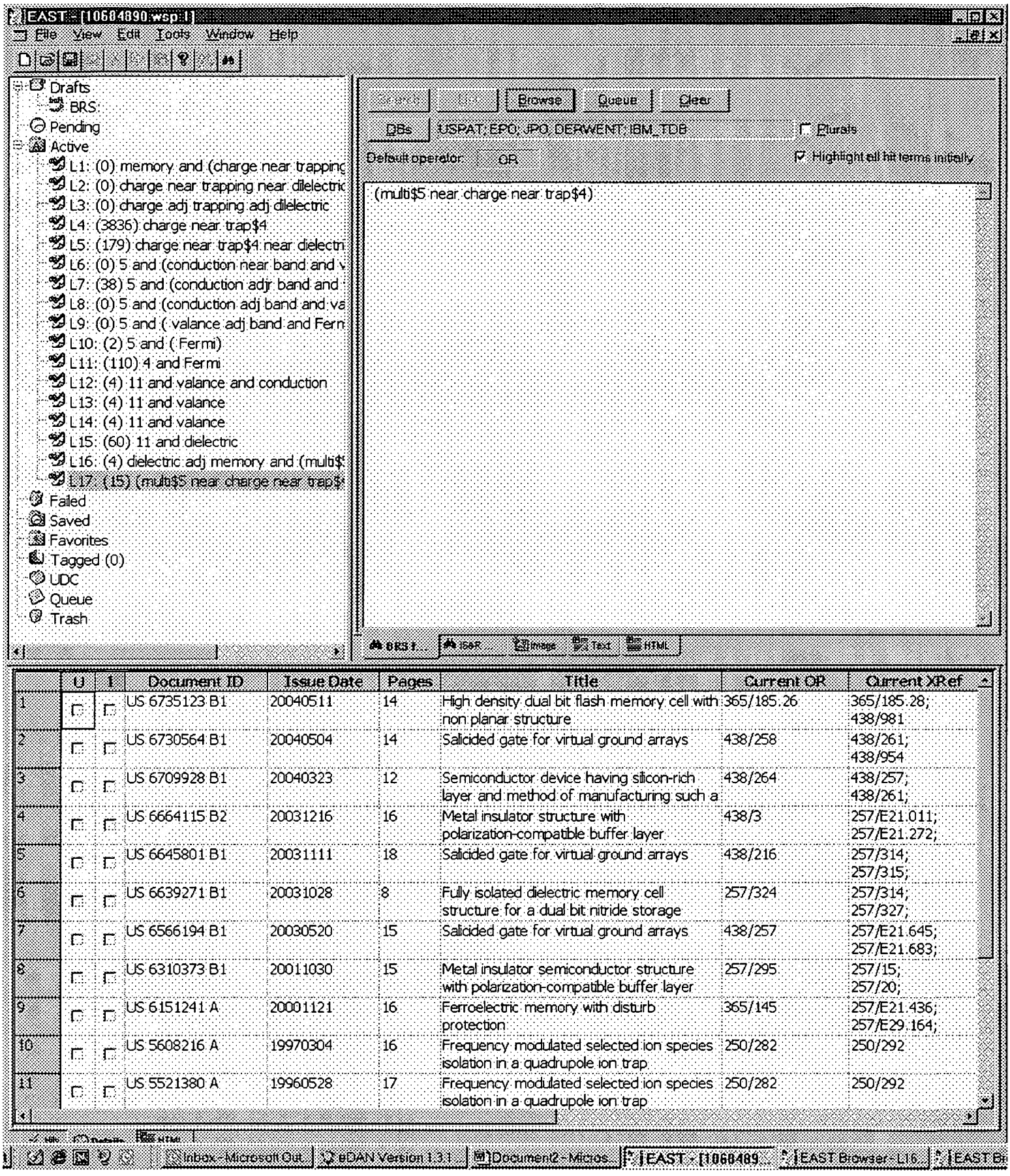

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	☐	☐	US 6735123 B1	20040511	14	High density dual bit flash memory cell with non planar structure	365/185.26	365/185.28; 438/981
2	☐	☐	US 6730564 B1	20040504	14	Salicided gate for virtual ground arrays	438/258	438/261; 438/954
3	☐	☐	US 6709928 B1	20040323	12	Semiconductor device having silicon-rich layer and method of manufacturing such a	438/264	438/257; 438/261;
4	☐	☐	US 6664115 B2	20031216	16	Metal insulator structure with polarization-compatible buffer layer	438/3	257/E21.011; 257/E21.272;
5	☐	☐	US 6645801 B1	20031111	18	Salicided gate for virtual ground arrays	438/216	257/314; 257/315;
6	☐	☐	US 6639271 B1	20031028	8	Fully isolated dielectric memory cell structure for a dual bit nitride storage	257/324	257/314; 257/327;
7	☐	☐	US 6566194 B1	20030520	15	Salicided gate for virtual ground arrays	438/257	257/E21.645; 257/E21.683;
8	☐	☐	US 6310373 B1	20011030	15	Metal insulator semiconductor structure with polarization-compatible buffer layer	257/295	257/15; 257/20;
9	☐	☐	US 6151241 A	20001121	16	Ferroelectric memory with disturb protection	365/145	257/E21.436; 257/E29.164;
10	☐	☐	US 5608216 A	19970304	16	Frequency modulated selected ion species isolation in a quadrupole ion trap	250/282	250/292
11	☐	☐	US 5521380 A	19960528	17	Frequency modulated selected ion species isolation in a quadrupole ion trap	250/282	250/292